

● General Description

The AGM1405F combines advanced trenchMOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
40V	3mΩ	130A

TO-220F Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM1405F	AGM1405F	TO-220F	----	----	1000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	40	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	130	A
	Drain Current-Continuous(Tc=100°C)	82	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	420	A
PD	Maximum Power Dissipation(Tc=25°C)	105	w
	Maximum Power Dissipation(Tc=100°C)	41	w
EAS	Avalanche energy (Note 3)	360	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	45	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	1.2	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=40V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.1	1.5	2.1	V
gFS	Forward Transconductance	VDS=5V, ID=20A	--	16	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	3.0	4.2	mΩ
		VGS=4.5V, ID=15A	--	3.5	4.9	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=15V, VGS=0V, F=1MHZ	--	2600	--	pF
Coss	Output Capacitance		--	370	--	pF
Crss	Reverse Transfer Capacitance		--	170	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	1.7	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V, VDS=15V, RGEN=3.3Ω RL=0.75Ω	--	6.9	--	nS
tr	Turn-on Rise Time		--	1.7	--	nS
td(off)	Turn-Off Delay Time		--	30	--	nS
tf	Turn-Off Fall Time		--	15	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=20V, ID=12A	--	20	--	nC
Qgs	Gate-Source Charge		--	9	--	nC
Qgd	Gate-Drain Charge		--	11	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)	VG=VD=0V, Force Current	--	--	130	A
VSD	Forward on Voltage	VGS=0V, IS=12A	--	--	1.2	V
trr	Reverse Recovery Time	IF=12A , dI/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

Fig.1 Power Dissipation

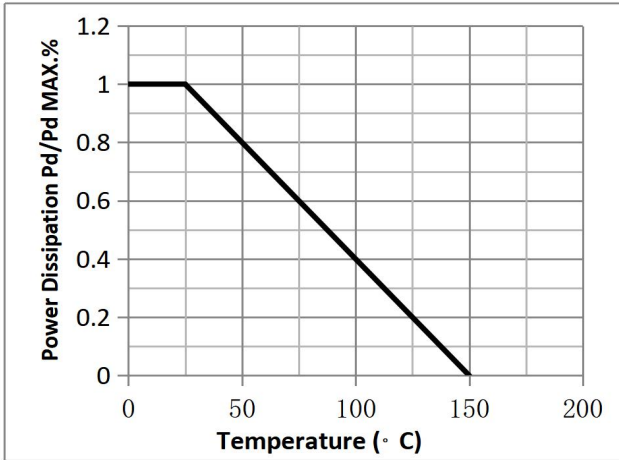


Fig.2 Typical output Characteristics

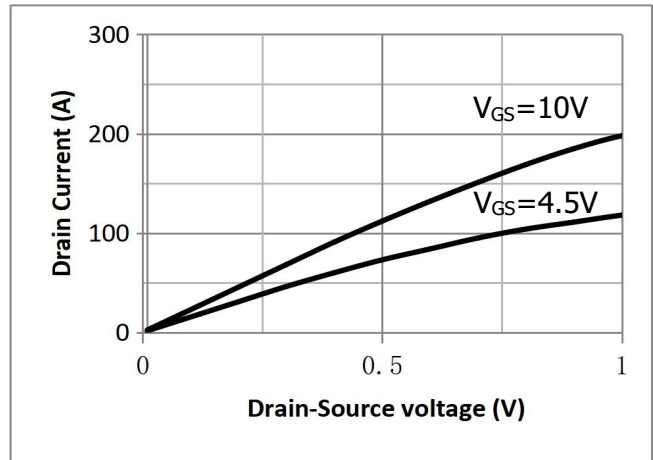


Fig.3 Threshold Voltage V.S Junction Temperature

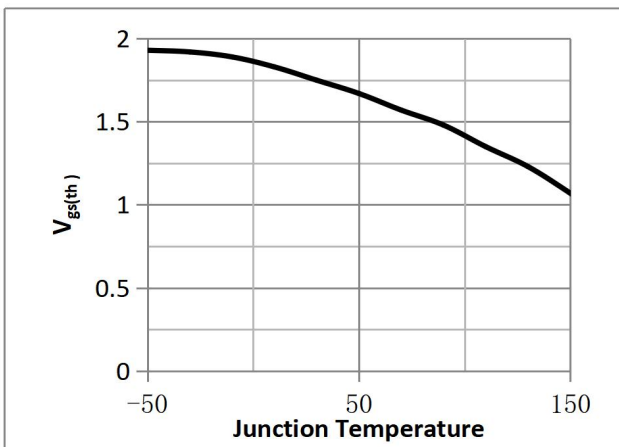


Fig.4 Resistance V.S Drain Current

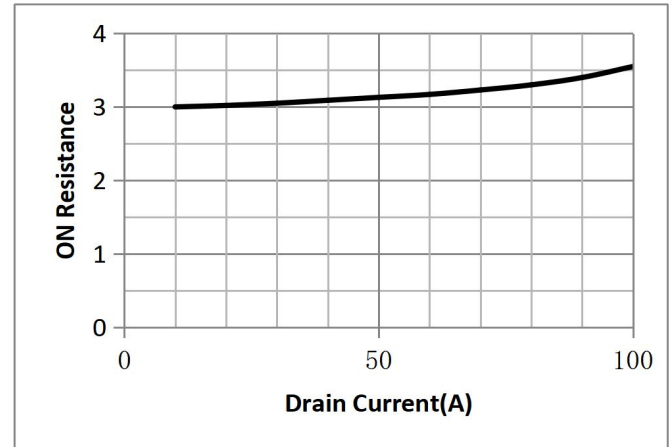


Fig.5 On-Resistance VS Gate Source Voltage

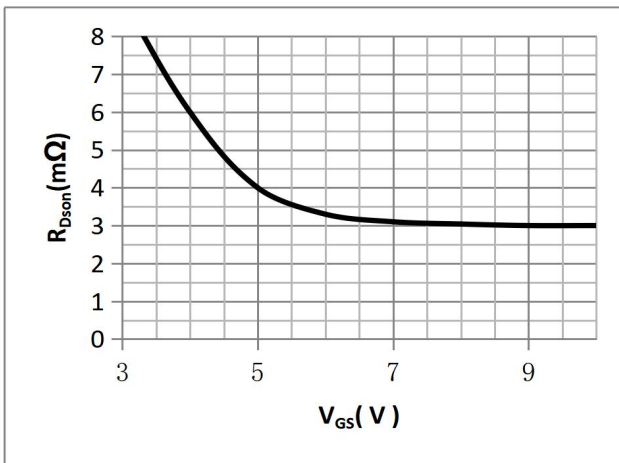


Fig.6 On-Resistance V.S Junction Temperature

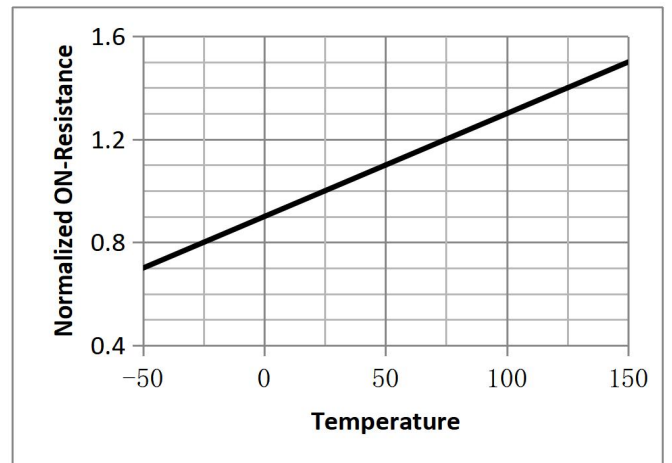


Fig.7 Switching Time Measurement Circuit

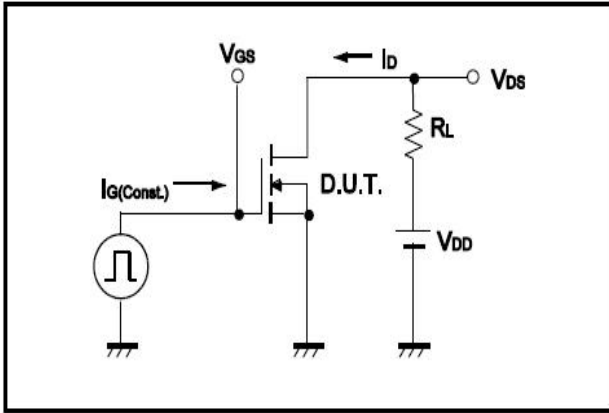


Fig.8 Gate Charge Waveform

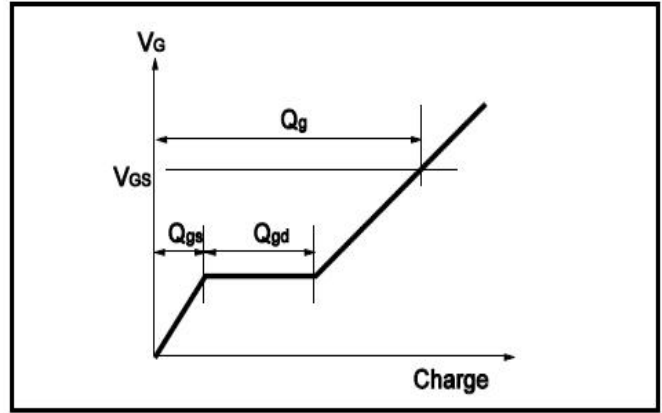


Fig.9 Switching Time Measurement Circuit

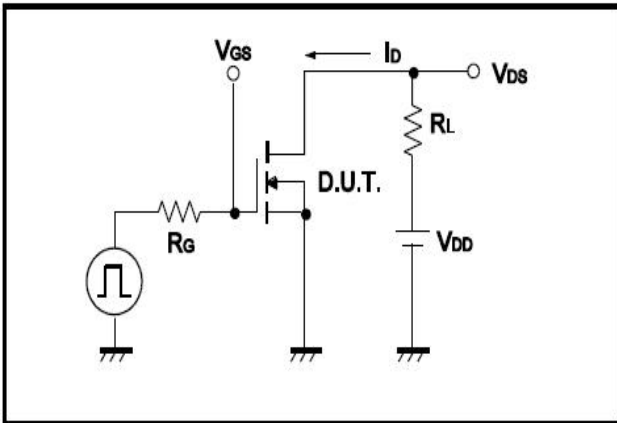


Fig.10 Gate Charge Waveform

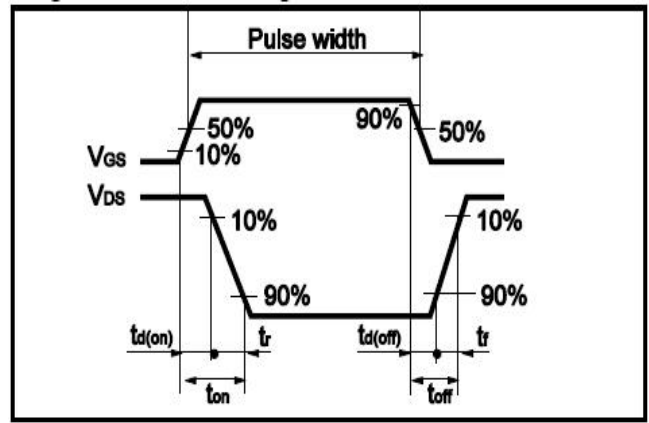


Fig.11 Avalanche Measurement Circuit

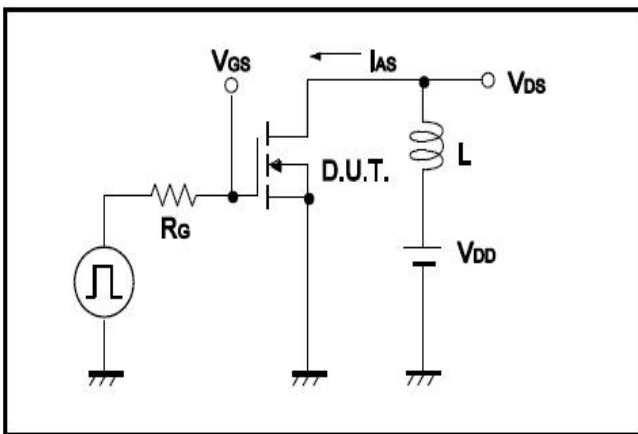
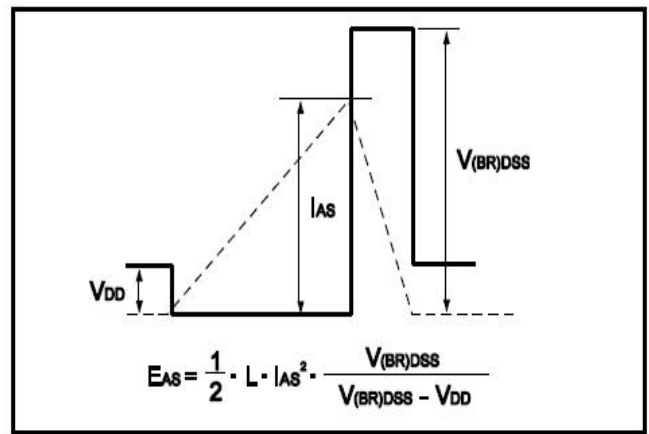


Fig.12 Avalanche Waveform



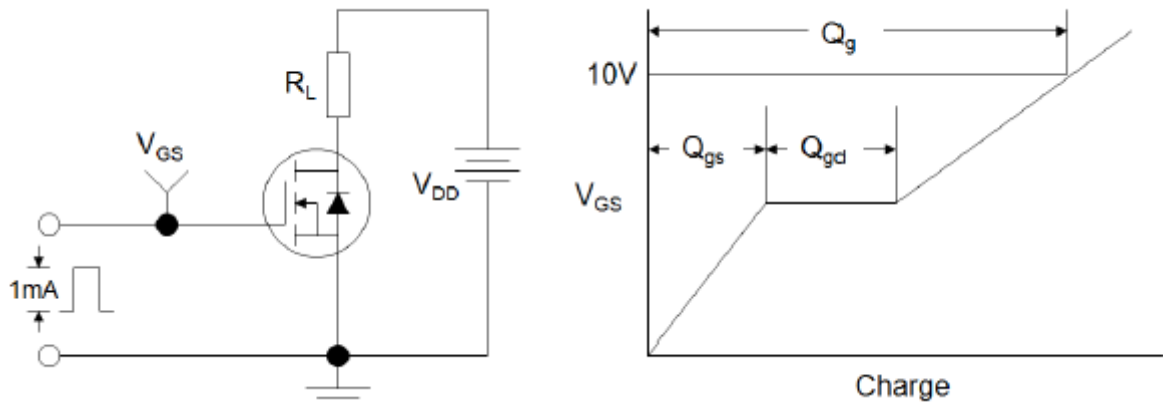


Figure 1: Gate Charge Test Circuit & Waveform

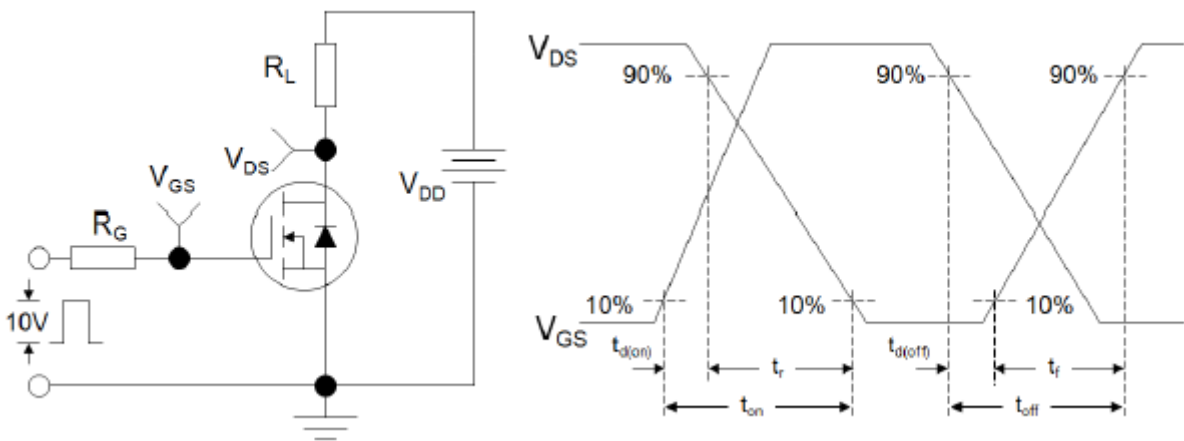


Figure 2: Resistive Switching Test Circuit & Waveforms

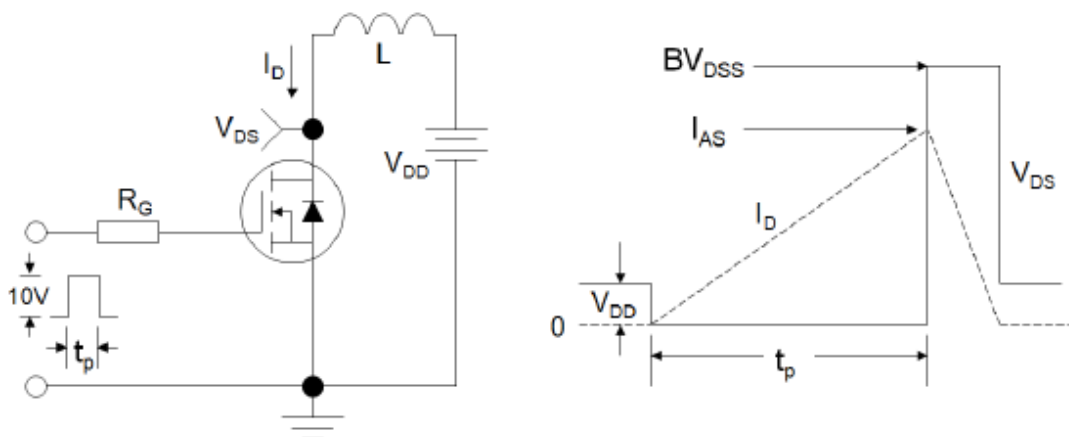
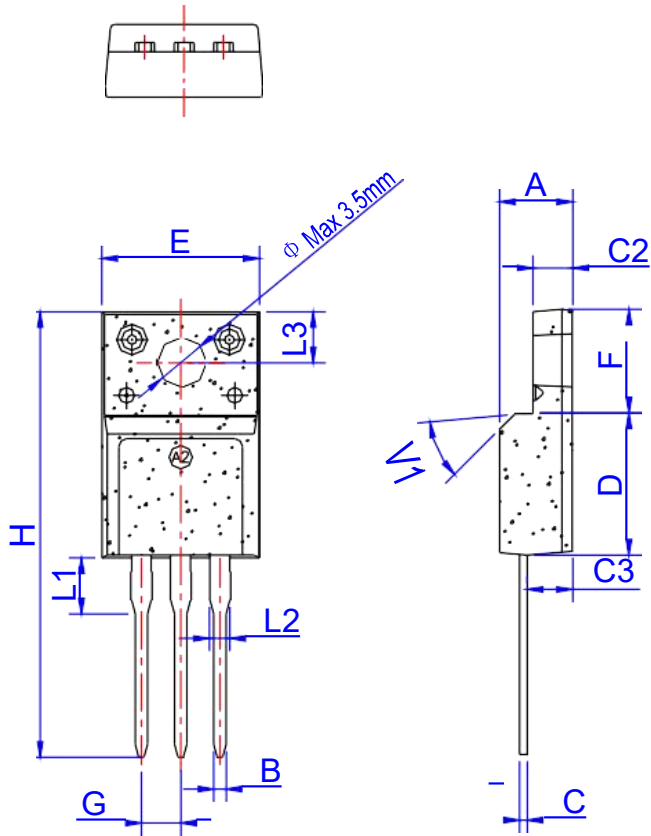


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

TO-220F Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	


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